Date Mailed: August 4, 2004

Sheet 1 of 1

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1440US01	Application Number: 10/809,033
	Applicant: SASAKI et al.	
	Filing Date: March 25, 2004	Group Art Unit: Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
D.H.	2000-233993	08.2000	Japan			Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

D.H.		Kurai et al., "Nucleation Control in the Growth of Bulk GaN by Submission Method", Jpn. J. Appl. Phys., Vol. 36 (1997), pp. L184-L186, Part 2, No. 2B, 15 February 1997
D.H.		Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (2002) 922-925.

EXAMINER	DATE CONSIDERED 3-4-6

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

*Substitute Disclosure Statement Form (PTO-1449)

Date Mailed: September 23, 2004

Sheet 1 of 1

FORM 1449 INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1440US01	Application Number: 10/809,033
	Applicant: SASAKI et al.	
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
D.H.	2004/013385	02.2004	WO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

D.H.		Imade et al., "Growth of Bulk GaN Single Crystals by High-Pressure Sublimation Method", Proceedings of the 48th Symposium on Synthetic Crystals, 1A06, pp 23-24
D.H.		Imade et al. "Growth of Thick GaN Films with High Growth Rate Using Sublimation Method under High Pressure", Jpn. J. Appl. Phys., Vol. 43 (2004), pp. L486-L488

EXAMINER	DATE CONSIDERED 3-4-6

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.